

4-Mb (256K x 16) Static RAM

Features

- **Very high speed: 55 ns and 70 ns**
- **Wide voltage range: 1.65V – 2.25V**
- **Pin-compatible with CY62147CV18**
- **Ultra-low active power**
 - Typical active current: 1 mA @ f = 1 MHz
 - Typical active current: 6 mA @ f = f_{max}
- **Ultra low standby power**
- **Easy memory expansion with \overline{CE} , and \overline{OE} features**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Packages offered 48-ball BGA**

Functional Description^[1]

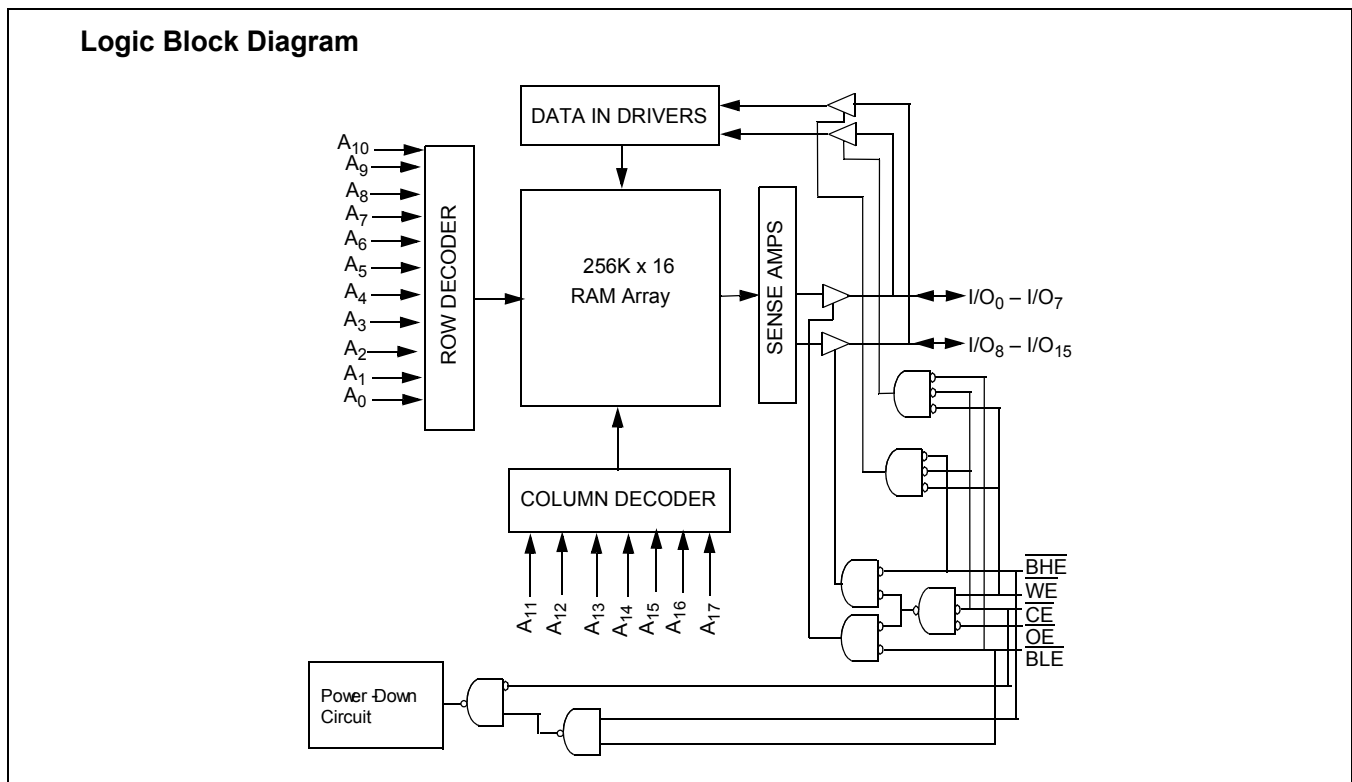
The CY62147DV18 is a high-performance CMOS static RAM organized as 256K words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL™) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption. The device can also be put into standby

mode reducing power consumption by more than 99% when deselected (\overline{CE} HIGH or both \overline{BLE} and \overline{BHE} are HIGH). The input/output pins (I/O₀ through I/O₁₅) are placed in a high-impedance state when: deselected (\overline{CE} HIGH), outputs are disabled (\overline{OE} HIGH), both Byte High Enable and Byte Low Enable are disabled (\overline{BHE} , \overline{BLE} HIGH), or during a write operation (\overline{CE} LOW and \overline{WE} LOW).

Writing to the device is accomplished by asserting Chip Enable (\overline{CE}) and Write Enable (\overline{WE}) inputs LOW. If Byte Low Enable (\overline{BLE}) is LOW, then data from I/O pins (I/O₀ through I/O₇), is written into the location specified on the address pins (A₀ through A₁₇). If Byte High Enable (\overline{BHE}) is LOW, then data from I/O pins (I/O₈ through I/O₁₅) is written into the location specified on the address pins (A₀ through A₁₇).

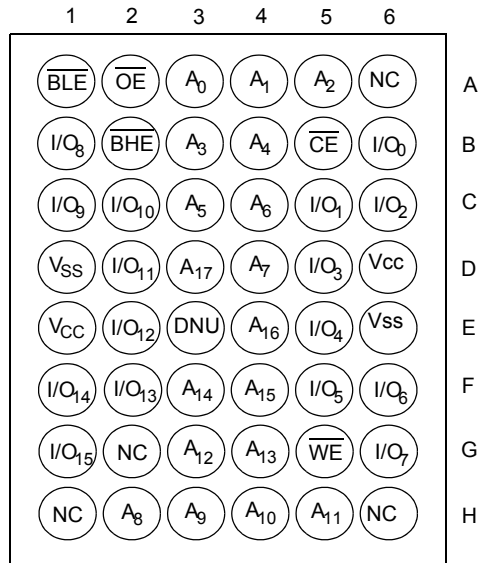
Reading from the device is accomplished by asserting Chip Enable (\overline{CE}) and Output Enable (\overline{OE}) LOW while forcing the Write Enable (\overline{WE}) HIGH. If Byte Low Enable (\overline{BLE}) is LOW, then data from the memory location specified by the address pins will appear on I/O₀ to I/O₇. If Byte High Enable (\overline{BHE}) is LOW, then data from memory will appear on I/O₈ to I/O₁₅. See the truth table for a complete description of read and write modes.

The CY62147DV18 is available in a 48-ball FBGA package.



Note:

1. For best practice recommendations, please refer to the Cypress application note "System Design Guidelines" on <http://www.cypress.com>.

Pin Configuration^[2, 3, 4]
FBGA (Top View)

Notes:

- NC pins are not internally connected on the die.
- DNU pins have to be left floating or tied to V_{SS} to ensure proper application.
- Pins H1, G2, and H6 in the BGA package are address expansion pins for 8 Mb, 16 Mb, and 32 Mb, respectively.



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

- Storage Temperature -65°C to + 150°C
- Ambient Temperature with Power Applied..... -55°C to + 125°C
- Supply Voltage to Ground Potential -0.2V to + V_{CC(MAX)} + 0.2V
- DC Voltage Applied to Outputs in High Z State^[5,6] -0.2V to V_{CC(MAX)} + 0.2V
- DC Input Voltage^[5,6] -0.2V to V_{CC (MAX)} + 0.2V

- Output Current into Outputs (LOW)..... 20 mA
- Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)
- Latch-up Current..... > 200 mA

Operating Range

Device	Range	Ambient Temperature (T _A)	V _{CC} ^[7]
CY62147DV18L	Industrial	-40°C to +85°C	1.65V to 2.25V
CY62147DV18LL			

Product Portfolio

Product	V _{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I _{CC} (mA)				Standby I _{SB2} (µA)	
	Min.	Typ. ^[7]	Max.		f = 1MHz		f = f _{max}			
					Typ. ^[7]	Max.	Typ. ^[7]	Max.	Typ. ^[7]	Max.
CY62147DV18L	1.65	1.8	2.25	55	1.0	2.0	6	15	0.5	18
10								12		
CY62147DV18LL	1.65	1.8	2.25	70	1.0	2.0	6	15	0.5	18
10								12		

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	CY62147DV18-55			CY62147DV18-70			Unit		
			Min.	Typ. ^[7]	Max.	Min.	Typ. ^[7]	Max.			
V _{OH}	Output HIGH Voltage	I _{OH} = -0.1 mA V _{CC} = 1.65V	1.4			1.4			V		
V _{OL}	Output LOW Voltage	I _{OL} = 0.1 mA V _{CC} = 1.65V			0.2			0.2	V		
V _{IH}	Input HIGH Voltage	V _{CC} = 1.65V to 2.25V	1.4		V _{CC} +0.2V	1.4		V _{CC} +0.2V	V		
V _{IL}	Input LOW Voltage	V _{CC} = 1.65V to 2.25V	-0.2		0.4	-0.2		0.4	V		
I _{IX}	Input Leakage Current	GND ≤ V _I ≤ V _{CC}	-1		+1	-1		+1	µA		
I _{OZ}	Output Leakage Current	GND ≤ V _O ≤ V _{CC} , Output Disabled	-1		+1	-1		+1	µA		
I _{CC}	V _{CC} Operating Supply Current	f = f _{MAX} = 1/t _{RC} V _{CC(max)} = 1.95V I _{OUT} = 0 mA CMOS levels	L		6	12		6	12	mA	
			LL			8			8		
			L		6	15		6	15	mA	
			LL			10			10		
		f = 1 MHz	V _{CC(max)} = 1.95V	L		1	1.5		1	1.5	mA
				LL							
V _{CC(max)} = 2.25V	L	L		1	2		1	2	mA		
		LL									

Notes:

5. V_{IL(min.)} = -2.0V for pulse durations less than 20 ns.
6. V_{IH(max.)} = V_{CC}+0.75V for pulse durations less than 20ns.
7. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ.)}, T_A = 25°C.

Electrical Characteristics Over the Operating Range (continued)

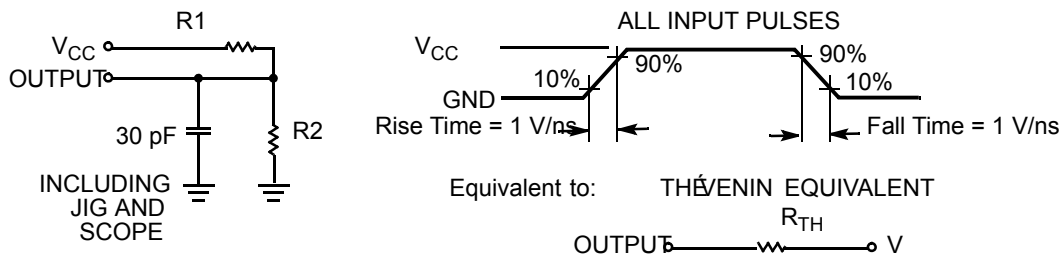
Parameter	Description	Test Conditions	CY62147DV18-55			CY62147DV18-70			Unit
			Min.	Typ. ^[7]	Max.	Min.	Typ. ^[7]	Max.	
I _{SB1}	Automatic CE Power-Down Current — CMOS Inputs	CE ≥ V _{CC} - 0.2V, V _{IN} ≥ V _{CC} - 0.2V, V _{IN} ≤ 0.2V; f = f _{MAX} (Address and Data Only), f = 0 (OE, WE, BHE and BLE)	V _{CC(max)} = 1.95V	L	0.5	12	0.5	12	μA
				LL					
			V _{CC(max)} = 2.25V	L	0.5	18	0.5	18	
				LL					
I _{SB2}	Automatic CE Power-down Current — CMOS Inputs	CE ≥ V _{CC} - 0.2V, V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V, f = 0	V _{CC(max)} = 1.95V	L	0.5	12	0.5	12	μA
				LL					
			V _{CC(max)} = 2.25V	L	0.5	18	0.5	18	
				LL					

Capacitance for all Packages^[8]

Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz,	10	pF
C _{OUT}	Output Capacitance	V _{CC} = V _{CC(typ)}	10	pF

Thermal Resistance

Parameter	Description	Test Conditions	BGA	Unit
θ _{JA}	Thermal Resistance (Junction to Ambient) ^[8]	Still Air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	75	°C/W
θ _{JC}	Thermal Resistance (Junction to Case) ^[8]		10	°C/W

AC Test Loads and Waveforms


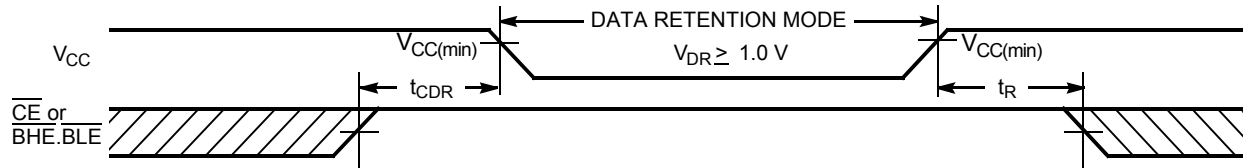
Parameters	1.80V	Unit
R1	13500	Ω
R2	10800	Ω
R _{TH}	6000	Ω
V _{TH}	0.80	V

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ. ^[7]	Max.	Unit
V _{DR}	V _{CC} for Data Retention		1.0			V
I _{CCDR}	Data Retention Current	V _{CC} = 1.0V CE ≥ V _{CC} - 0.2V, V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V	L		6	μA
			LL		4	
t _{CDR} ^[8]	Chip Deselect to Data Retention Time		0			ns
t _R	Operation Recovery Time		t _{RC}			ns

Notes:

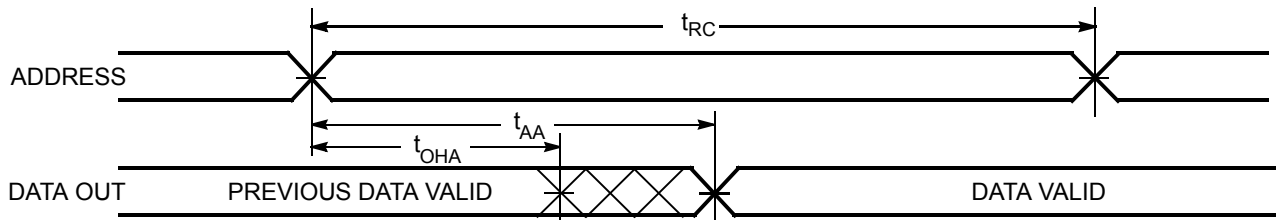
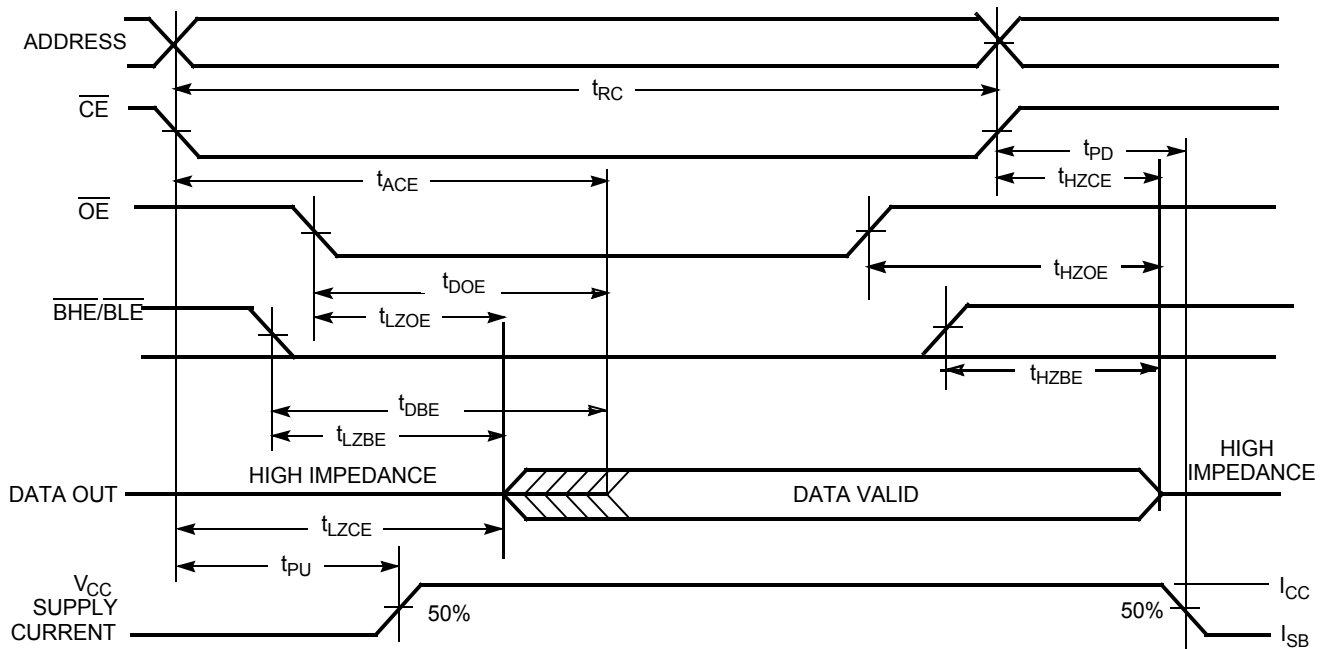
8. Tested initially and after any design or process changes that may affect these parameters.

Data Retention Waveform^[9]

Switching Characteristics Over the Operating Range^[10]

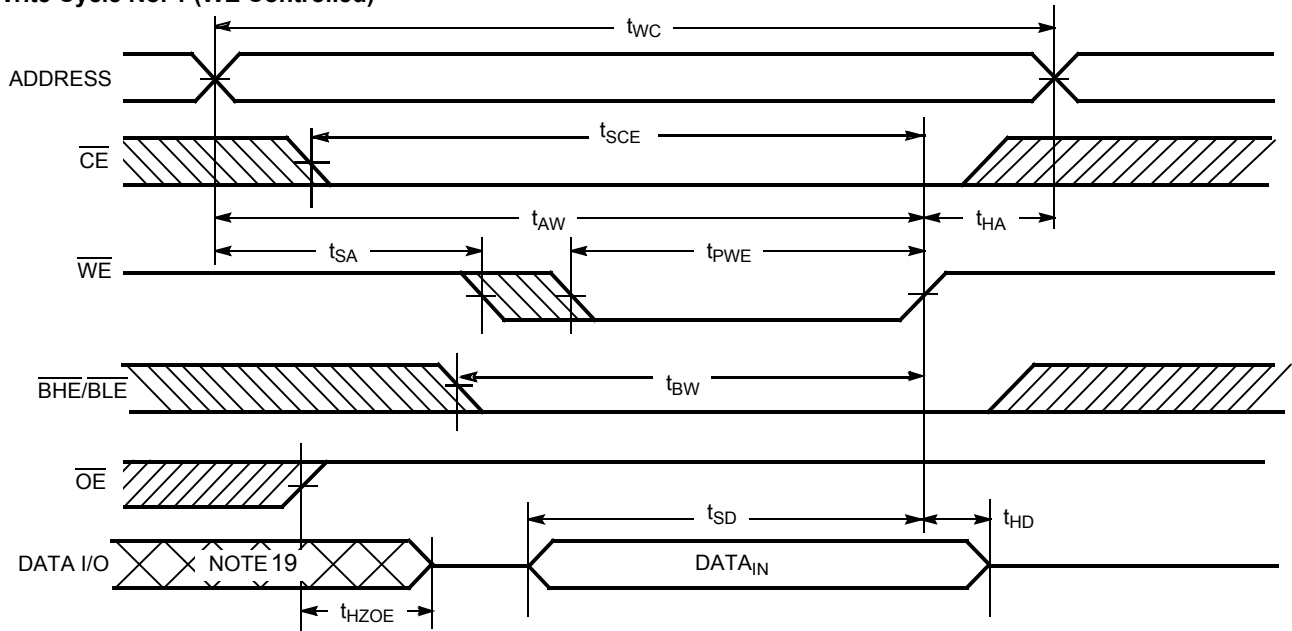
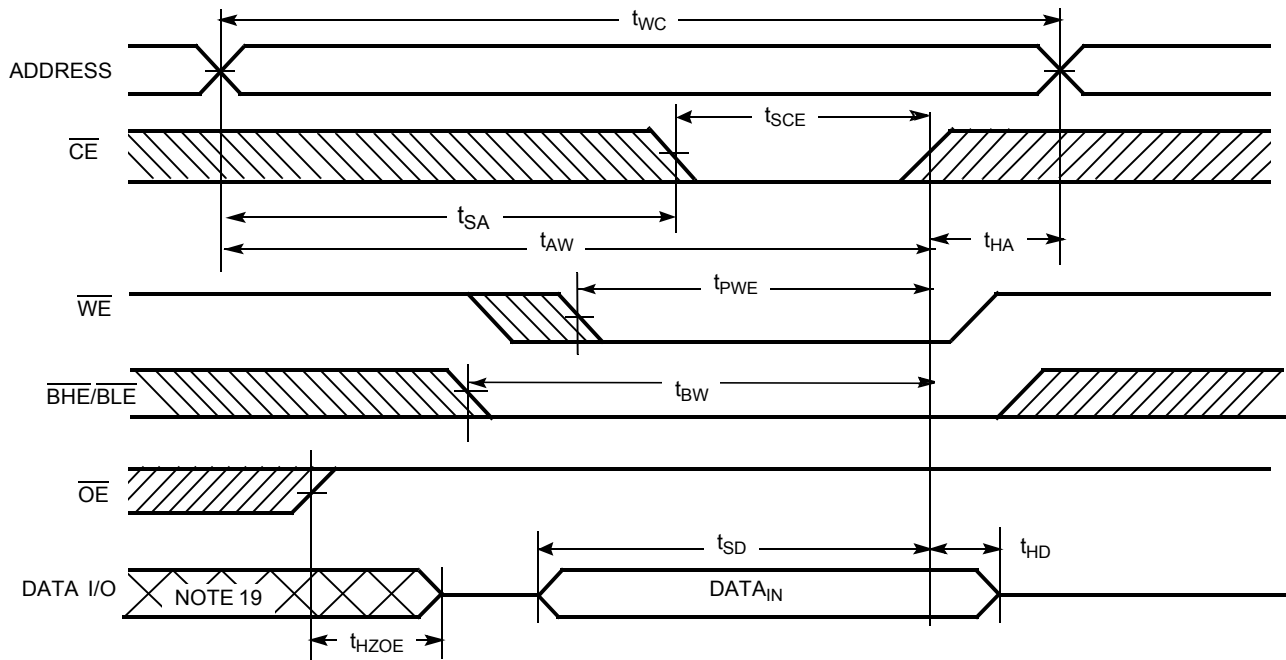
Parameter	Description	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
Read Cycle						
t_{RC}	Read Cycle Time	55		70		ns
t_{AA}	Address to Data Valid		55		70	ns
t_{OHA}	Data Hold from Address Change	10		10		ns
t_{ACE}	CE LOW to Data Valid		55		70	ns
t_{DOE}	OE LOW to Data Valid		25		35	ns
t_{LZOE}	OE LOW to Low Z ^[11]	5		5		ns
t_{HZOE}	OE HIGH to High Z ^[11, 12]		16		16	ns
t_{LZCE}	CE LOW to Low Z ^[11]	10		10		ns
t_{HZCE}	CE HIGH to High Z ^[11, 12]		20		25	ns
t_{PU}	CE LOW to Power-Up	0		0		ns
t_{PD}	CE HIGH to Power-Down		55		70	ns
t_{DBE}	BLE / BHE LOW to Data Valid		55		70	ns
t_{LZBE}	BLE / BHE LOW to Low Z ^[11]	10		10		ns
t_{HZBE}	BLE / BHE HIGH to HIGH Z ^[11, 12]		20		25	ns
Write Cycle^[13]						
t_{WC}	Write Cycle Time	55		70		ns
t_{SCE}	CE LOW to Write End	40		50		ns
t_{AW}	Address Set-up to Write End	40		50		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-up to Write Start	0		0		ns
t_{PWE}	WE Pulse Width	40		45		ns
t_{BW}	BLE / BHE LOW to Write End	40		50		ns
t_{SD}	Data Set-Up to Write End	25		30		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	WE LOW to High-Z ^[11, 12]		20		25	ns
t_{LZWE}	WE HIGH to Low-Z ^[11]	10		10		ns

Notes:

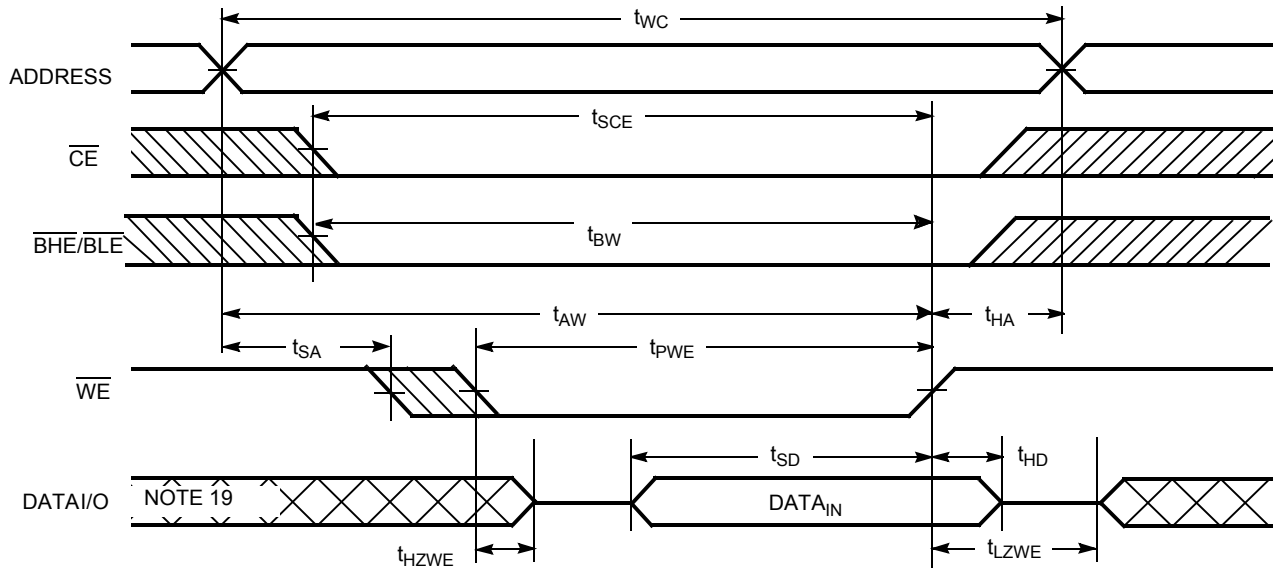
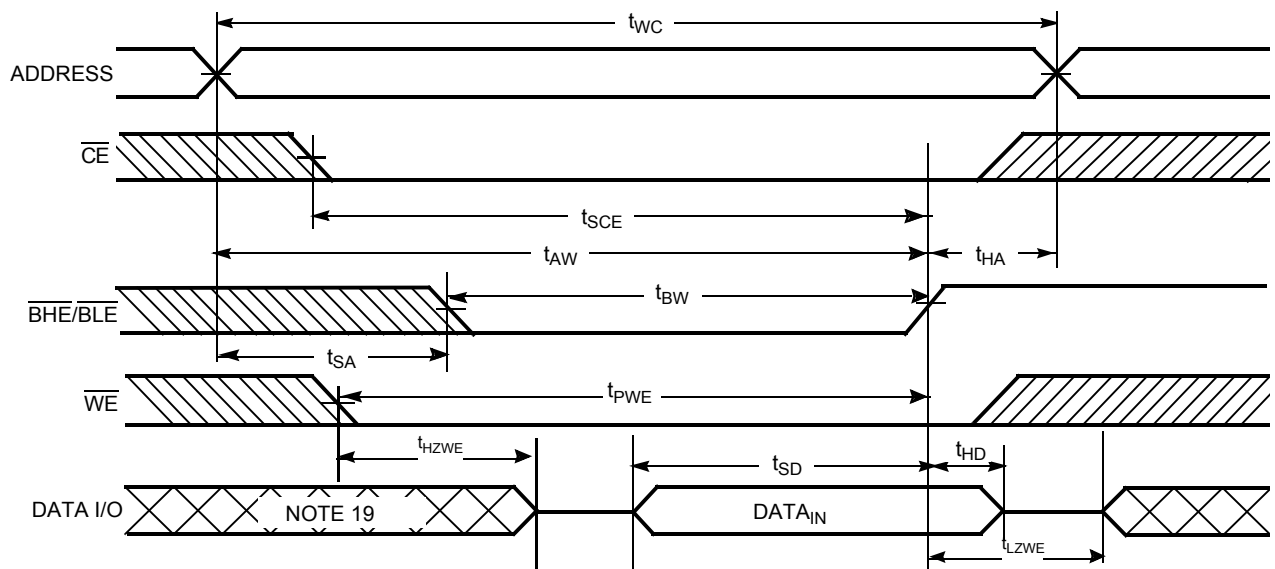
- $\overline{\text{BHE}}.\overline{\text{BLE}}$ is the AND of both $\overline{\text{BHE}}$ and $\overline{\text{BLE}}$. Chip can be deselected by either disabling the chip enable signal or by disabling both $\overline{\text{BHE}}$ and $\overline{\text{BLE}}$.
- Test conditions for all parameters other than three-state parameters assume signal transition time of 1V/ns or less, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0 to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the "AC Test Loads and Waveforms" section.
- At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZBE} is less than t_{LZBE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
- t_{HZOE} , t_{HZCE} , t_{HZBE} , and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
- The internal Write time of the memory is defined by the overlap of WE, CE = V_{IL} , BHE and/or BLE = V_{IL} . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Waveforms
Read Cycle 1 (Address Transition Controlled)^[14, 15]

Read Cycle No. 2 (\overline{OE} Controlled)^[15, 16]

Notes:

14. The device is continuously selected. \overline{OE} , $\overline{CE} = V_{IL}$, \overline{BHE} and/or $\overline{BLE} = V_{IL}$.
15. \overline{WE} is HIGH for read cycle.
16. Address valid prior to or coincident with \overline{CE} and \overline{BHE} , \overline{BLE} transition LOW.

Switching Waveforms (continued)
Write Cycle No. 1 (\overline{WE} Controlled) ^[13, 17, 18]

Write Cycle No. 2 (\overline{CE} Controlled) ^[13, 17, 18]

Notes:

17. Data I/O is high impedance if $\overline{OE} = V_{IH}$.
18. If \overline{CE} goes HIGH simultaneously with $\overline{WE} = V_{IH}$, the output remains in a high-impedance state.
19. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)
Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW) ^[18]

Write Cycle No. 4 ($\overline{BHE}/\overline{BLE}$ Controlled, \overline{OE} LOW) ^[18]


Truth Table

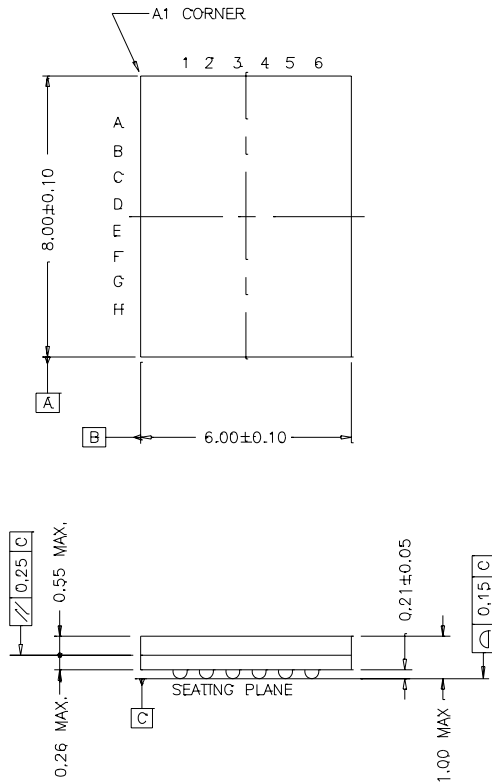
\overline{CE}	\overline{WE}	\overline{OE}	\overline{BHE}	\overline{BLE}	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
X	X	X	H	H	High Z	Deselect/Power-Down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O_0 – I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O_0 – I/O_7); I/O_8 – I/O_{15} in High Z	Read (Lower byte only)	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8 – I/O_{15}); I/O_0 – I/O_7 in High Z	Read (Higher byte only)	Active (I_{CC})
L	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	L	H	High Z	Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O_0 – I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O_0 – I/O_7); I/O_8 – I/O_{15} in High Z	Write (Lower byte only)	Active (I_{CC})
L	L	X	L	H	Data In (I/O_8 – I/O_{15}); I/O_0 – I/O_7 in High Z	Write (Higher byte only)	Active (I_{CC})

Ordering Information

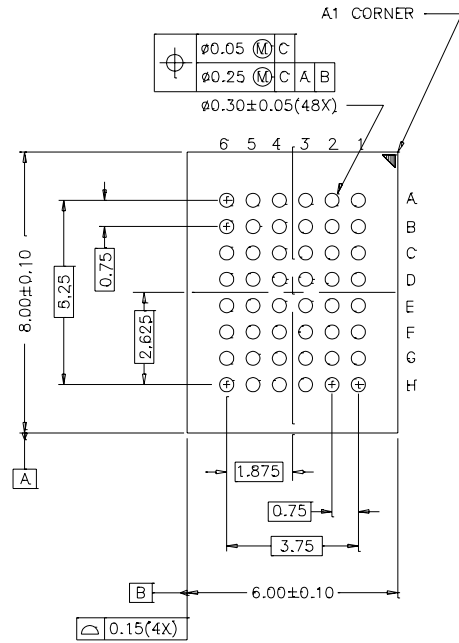
Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
55	CY62147DV18L-55BVI	BV48A	48-ball Fine Pitch BGA (6 mm × 8mm × 1 mm)	Industrial
	CY62147DV18LL-55BVI			
70	CY62147DV18L-70BVI	BV48A	48-ball Fine Pitch BGA (6 mm × 8mm × 1 mm)	Industrial
	CY62147DV18LL-70BVI			
55	CY62147DV18L-55BVXI	BV48A	48-ball Fine Pitch BGA (6 mm × 8mm × 1 mm) Pb-free	Industrial
	CY62147DV18LL-55BVXI			
70	CY62147DV18L-70BVXI	BV48A	48-ball Fine Pitch BGA (6 mm × 8mm × 1 mm) Pb-free	Industrial
	CY62147DV18LL-70BVXI			

Package Diagram
48-Lead VFBGA (6 x 8 x 1 mm) BV48A

TOP VIEW



BOTTOM VIEW



51-85150-*B

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Document History Page

Document Title: CY62147DV18 MoBL2™ 4-Mb (256K x 16) Static RAM				
Document Number: 38-05343				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	127482	06/17/03	HRT	New Data Sheet
*A	131009	11/26/03	CBD	Changed From Advance to Preliminary
*B	229908	See ECN	AJU	Changed From Preliminary to Final Added 70 ns speed bin Changed V _{CC} MAX spec from 2.20V to 2.25V Modified V _{IH} spec on footnote #6 from V _{CC(MAX)} + 0.5V to V _{CC(MAX)} + 0.75V Changed I _{CC} TYP values from 8 mA to 6 mA Changed I _{CC} MAX values at V _{CC} (max) = 1.95V from 15 mA to 12 mA (L bin) and 10 mA to 8mA (LL bin) Changed I _{CC} MAX values at V _{CC} (max) = 2.25V from 18 mA to 15 mA (L bin) and 12mA to 10 mA (LL bin) With modified V _{CC} MAX spec, changed I _{SB1} and I _{SB2} MAX values from 15 uA to 18 uA (L bin) and 10 uA to 12 uA (LL bin) Modified input and output capacitance values Removed footnote #9 from earlier rev Removed MAX value for V _{DR} Modified t _{HZOE} from 20 ns to 16 ns Added Pb-free ordering information